High-temperature 60 V, 3 A Schottky barrier rectifier 15 October 2012

Product data sheet

Product profile 1.

1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a SOD128 small and flat lead Surface-Mounted Device (SMD) plastic package.

1.2 Features and benefits

- Average forward current: $I_{F(AV)} \le 3 A$ •
- Reverse voltage: $V_R \le 60 V$ •
- Low forward voltage
- . High power capability due to clip-bonding technology
- Small and flat lead SMD plastic package
- AEC-Q101 qualified •
- High temperature T_i ≤ 175 °C

1.3 Applications

- Low voltage rectification •
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Reverse polarity protection

1.4 Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _F	forward current	T _{sp} = 160 °C		-	-	4.2	А
$I_{F(AV)}$	average forward current	δ = 0.5 ; f = 20 kHz; T _{amb} ≤ 80 °C; square wave	[1]	-	-	3	А
		δ = 0.5 ; f = 20 kHz; T _{sp} ≤ 165 °C; square wave		-	-	3	А
V _R	reverse voltage	T _j = 25 °C		-	-	60	V
V _F	forward voltage	I _F = 3 A; T _j = 25 °C		-	460	530	mV
I _R	reverse current	$\label{eq:transform} \begin{array}{l} T_{j} = 25 \ ^{\circ}\text{C}; \ V_{\text{R}} = 60 \ \text{V}; \ t_{p} \leq 300 \ \mu\text{s}; \\ \delta \leq 0.02 \ ; \ \text{pulsed} \end{array}$		-	80	200	μA







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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t _{rr}	reverse recovery time	$I_R = 0.5 \text{ A}; I_F = 0.5 \text{ A}; I_{R(meas)} = 0.1 \text{ A};$	-	12	-	ns
		T _j = 25 °C				

[1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.

2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode[1]		1 🛃 2
2	А	anode		sym001
			SOD128	

[1] The marking bar indicates the cathode.

3. Ordering information

Table 3. Ordering information				
Type number	Package			
	Name	Description	Version	
PMEG6030ETP	SOD128	plastic surface-mounted package; 2 leads	SOD128	

4. Marking

Table 4. Marking codes	
Type number	Marking code
PMEG6030ETP	DA

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _R	reverse voltage	T _j = 25 °C		-	60	V
I _F	forward current	T _{sp} = 160 °C		-	4.2	А
I _{F(AV)}	average forward current	δ = 0.5 ; f = 20 kHz; T _{amb} ≤ 80 °C; square wave	[1]	-	3	A
		δ = 0.5 ; f = 20 kHz; T _{sp} ≤ 165 °C; square wave		-	3	A
I _{FSM}	non-repetitive peak forward current	t_p = 8 ms; $T_{j(init)}$ = 25 °C; square wave		-	50	A
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Symbol	Parameter	Conditions		Min	Max	Unit
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[2]	-	750	mW
		[3]	-	1250	mW	
		[1]	-	2500	mW	
Т _ј	junction temperature			-	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C

[1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

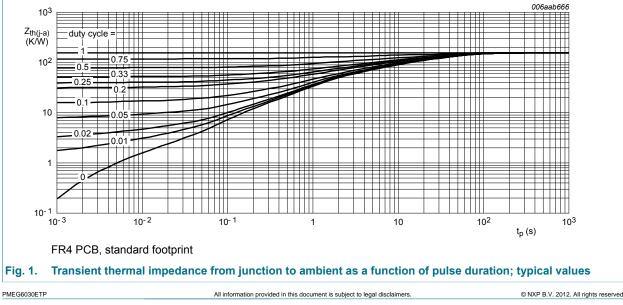
[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

6. Thermal characteristics

Table 6. Thermal characteristics							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
ui(j-u)	thermal resistance	-	[1][2]	-	-	200	K/W
	from junction to		[1][3]	-	-	120	K/W
	ampient		[1][4]	-	-	60	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		[5]	-	-	12	K/W

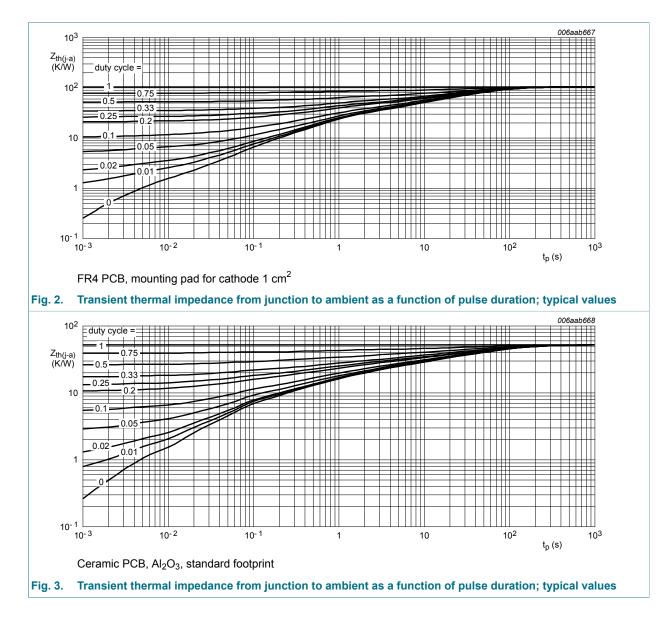
[1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.

- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².
- [4] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- [5] Soldering point of cathode tab.



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7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _F forward voltage	I _F = 0.1 A; T _j = 25 °C	-	290	330	mV	
		I _F = 0.5 A; T _j = 25 °C	-	340	400	mV
		I _F = 1 A; T _j = 25 °C	-	380	440	mV
		I _F = 1.5 A; T _j = 25 °C	-	400	470	mV
		I _F = 2 A; T _j = 25 °C	-	430	500	mV
		I _F = 3 A; T _j = 25 °C	-	460	530	mV

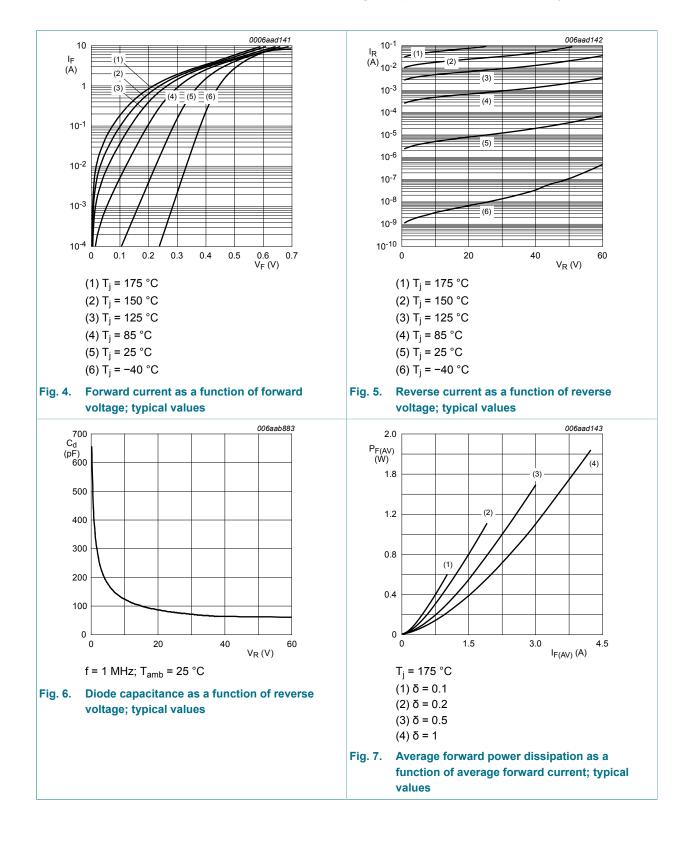
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		I _F = 3 A; T _j = -40 °C	-	510	590	mV
		I _F = 3 A; T _j = 125 °C	-	405	480	mV
	I _F = 3 A; T _j = 150 °C	-	390	460	mV	
	I _F = 3 A; T _j = 175 °C	-	370	450	mV	
I _R reverse current	reverse current	V_R = 5 V; T _j = 25 °C; t _p ≤ 300 µs; $\delta \le 0.02$; pulsed	-	4	-	μA
		V_R = 10 V; T _j = 25 °C; t _p ≤ 300 µs; δ ≤ 0.02 ; pulsed	-	5	-	μA
		V_R = 60 V; T _j = 25 °C; t _p ≤ 300 µs; $\delta \le 0.02$; pulsed	-	80	200	μA
		V_R = 60 V; T _j = -40 °C; t _p ≤ 300 µs; $\delta \le 0.02$; pulsed	-	0.5	10	μA
		V_R = 60 V; T _j = 125 °C; t _p ≤ 300 µs; $\delta \le 0.02$; pulsed	-	45	150	mA
C _d	diode capacitance	V _R = 1 V; f = 1 MHz; T _j = 25 °C	-	360	-	pF
		V _R = 10 V; f = 1 MHz; T _j = 25 °C	-	120	-	pF
t _{rr}	reverse recovery time	$I_{F} = 0.5 \text{ A}; I_{R} = 0.5 \text{ A}; I_{R(meas)} = 0.1 \text{ A};$ $T_{j} = 25 \text{ °C}$	-	12	-	ns
V _{FRM}	peak forward recovery voltage	$I_F = 1 \text{ A}; \text{ d}_F/\text{d}t = 40 \text{ A}/\mu\text{s}; \text{ T}_j = 25 ^\circ\text{C}$	-	425	-	mV

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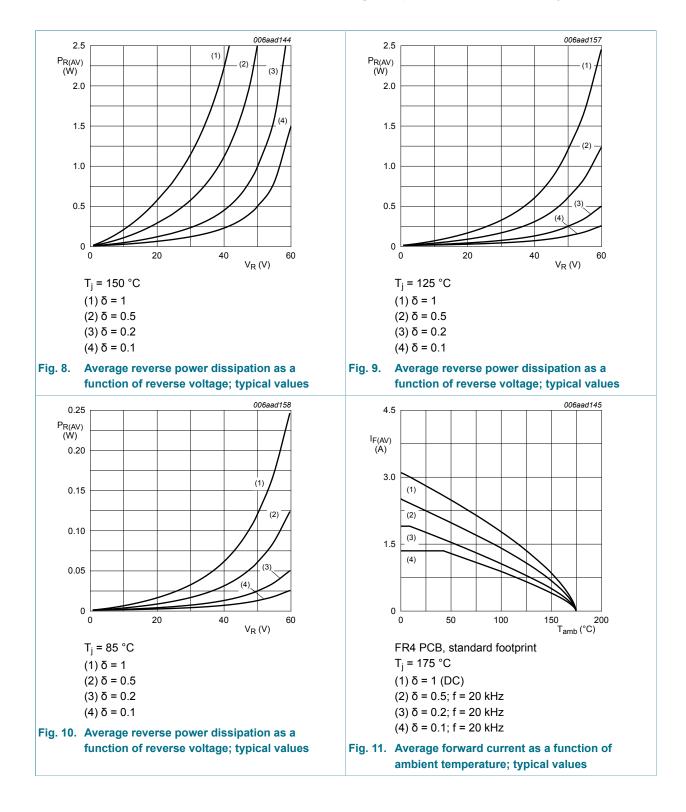


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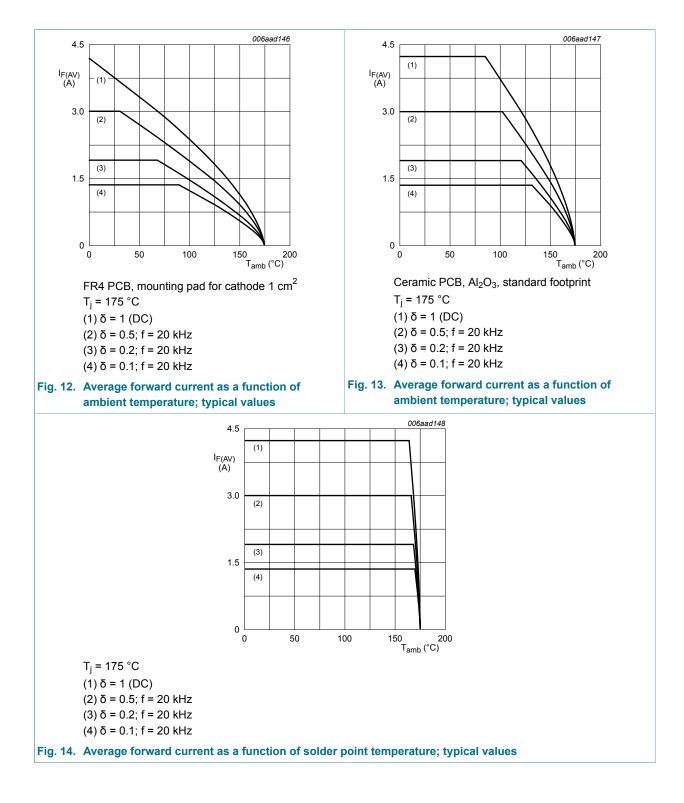


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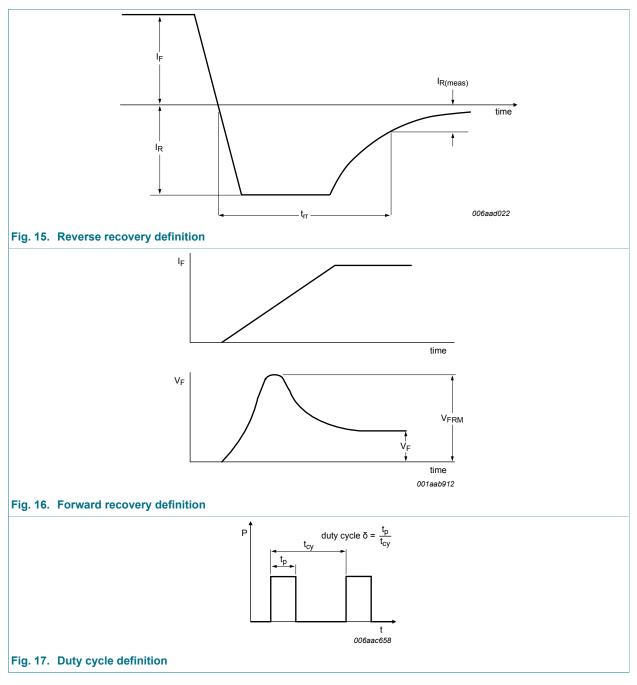


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Test information 8.



The current ratings for the typical waveforms are calculated according to the equations: $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current, $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

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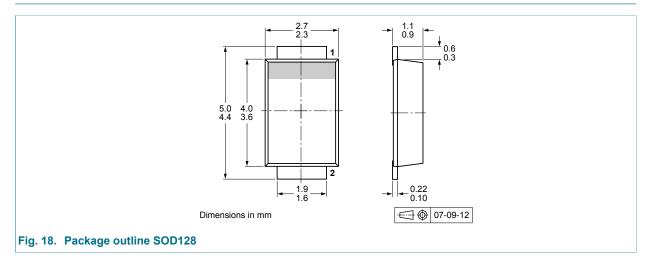
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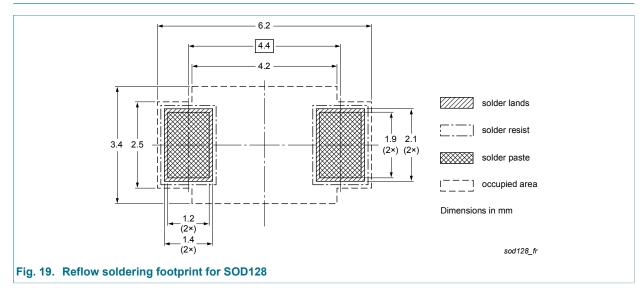
8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

9. Package outline



10. Soldering



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11. PMEG6030ETP

Table 8. Revision his	Ible 8. Revision history					
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PMEG6030ETP v.1	20121015	Product data sheet	-	-		

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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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